



N-Channel 20-V (D-S) MOSFET

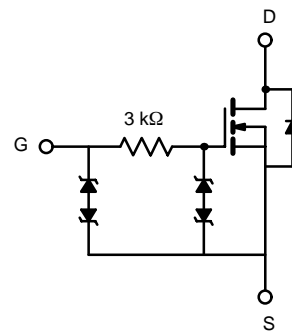
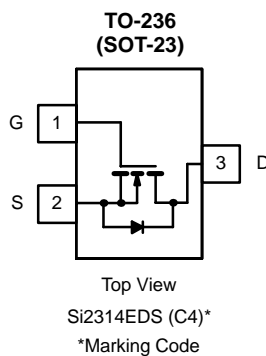
PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
20	0.033 @ $V_{GS} = 4.5$ V	4.9
	0.040 @ $V_{GS} = 2.5$ V	4.4
	0.051 @ $V_{GS} = 1.8$ V	3.9

FEATURES

- TrenchFET® Power MOSFET
- ESD Protected: 3000 V

APPLICATIONS

- Li-Ion Battery Protection



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	5 sec	Steady State	Unit	
Drain-Source Voltage	V_{DS}	20		V	
Gate-Source Voltage	V_{GS}	± 12			
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	I_D	$T_A = 25^\circ\text{C}$	4.9	3.77	A
		$T_A = 70^\circ\text{C}$	3.9	3.0	
Pulsed Drain Current ^b	I_{DM}	15			
Avalanche Current ^b	I_{AS}	15			
Single Avalanche Energy	E_{AS}	L = 0.1 mH	11.25		mJ
Continuous Source Current (Diode Conduction) ^a			I_S	1.0	
Power Dissipation ^a	P_D	$T_A = 25^\circ\text{C}$	1.25	0.75	W
		$T_A = 70^\circ\text{C}$	0.80	0.48	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150		$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R_{thJA}	75	100	$t \leq 5$ sec	$^\circ\text{C/W}$
				Steady State	
Maximum Junction-to-Foot	R_{thJF}	40	50		

Notes

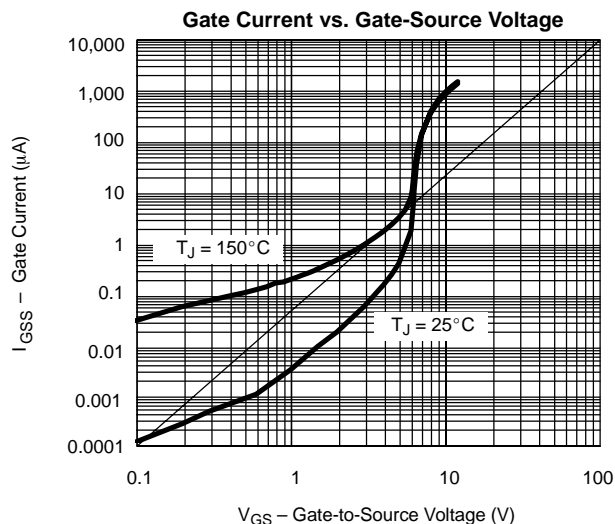
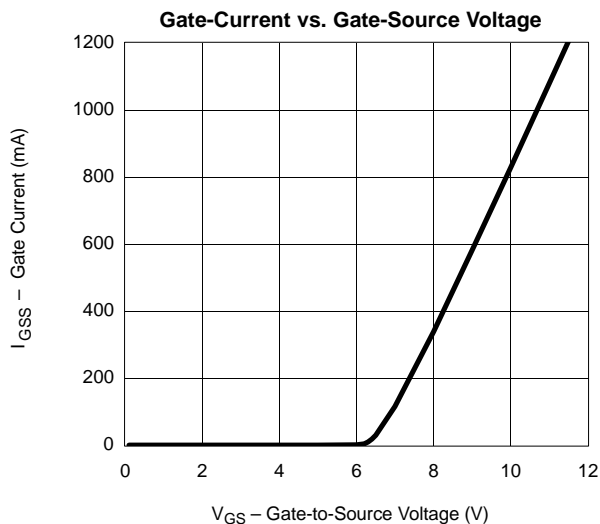
- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

SPECIFICATIONS (T _A = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	20			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.45			
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±4.5 V			±1.5	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 16 V, V _{GS} = 0 V			1	
		V _{DS} = 16 V, V _{GS} = 0 V, T _J = 70 °C			75	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 4.5 V	15			A
Drain-Source On-Resistance ^a	r _{DS(on)}	V _{GS} = 4.5 V, I _D = 5.0 A		0.027	0.033	Ω
		V _{GS} = 2.5 V, I _D = 4.5 A		0.033	0.040	
		V _{GS} = 1.8 V, I _D = 4.0 A		0.042	0.051	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 5.0 A		40		S
Diode Forward Voltage	V _{SD}	I _S = 1.0 A, V _{GS} = 0 V		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 5.0 A		11.0	14.0	nC
Gate-Source Charge	Q _{gs}			1.5		
Gate-Drain Charge	Q _{gd}			2.1		
Switching						
Turn-On Delay Time	t _{d(on)}	V _{DD} = 10 V, R _L = 10 Ω I _D ≅ 1.0 A, V _{GEN} = 4.5 V, R _G = 6 Ω		0.53	0.8	ns
Rise Time	t _r			1.4	2.2	
Turn-Off Delay Time	t _{d(off)}			13.5	20	
Fall-Time	t _f			5.9	9	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.0 A, di/dt = 100 A/μs		13	25	

Notes

- a. Pulse test: PW ≤ 300 μs duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

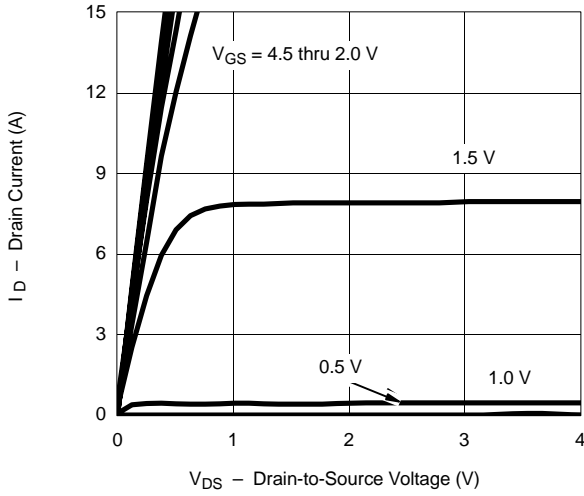
TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



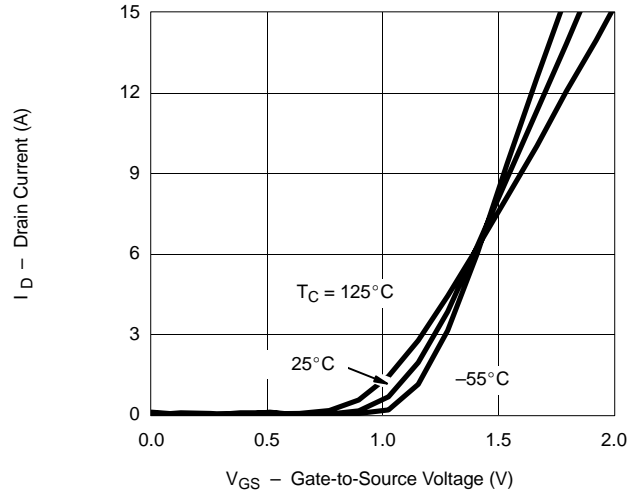


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

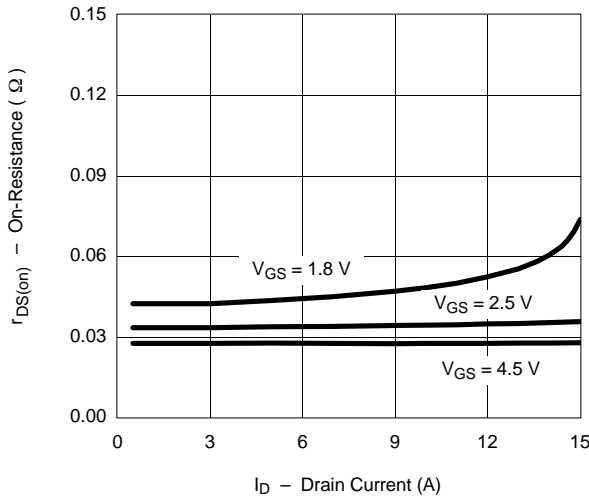
Output Characteristics



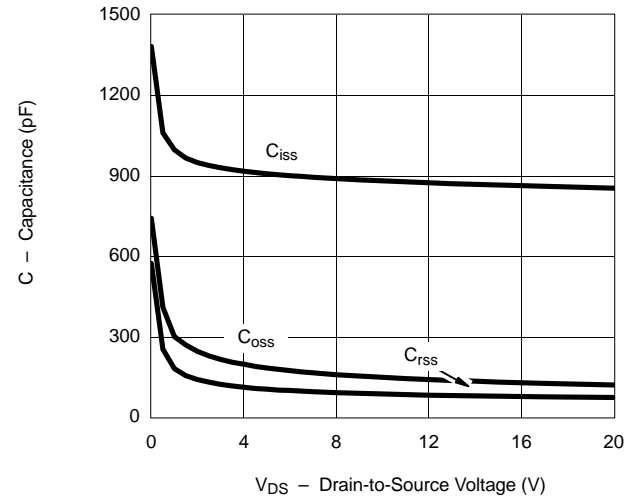
Transfer Characteristics



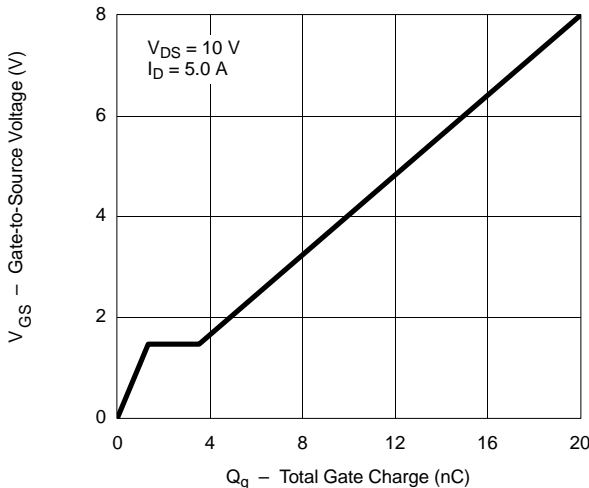
On-Resistance vs. Drain Current



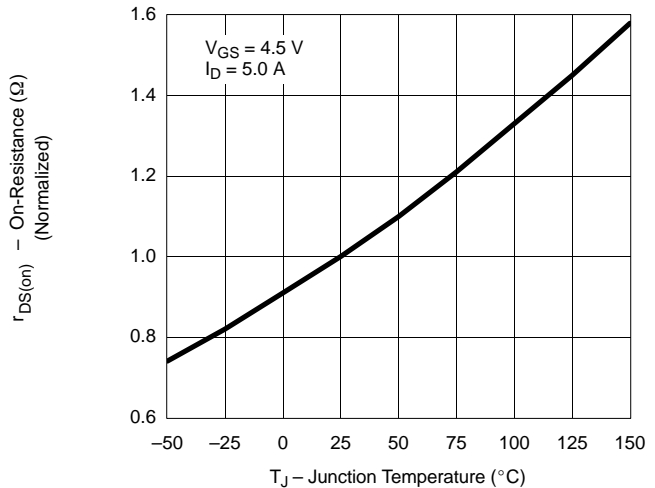
Capacitance



Gate Charge

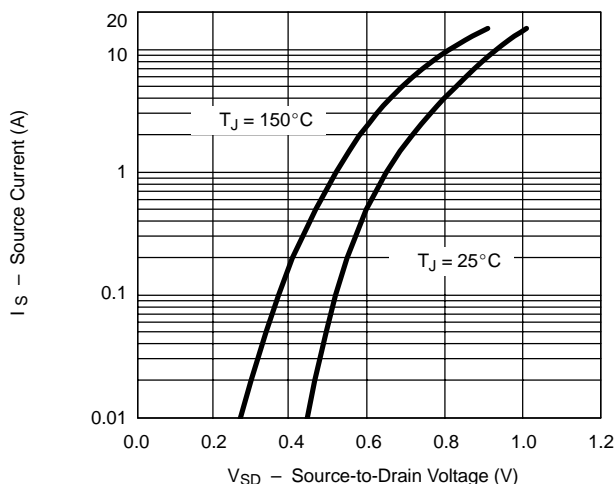


On-Resistance vs. Junction Temperature

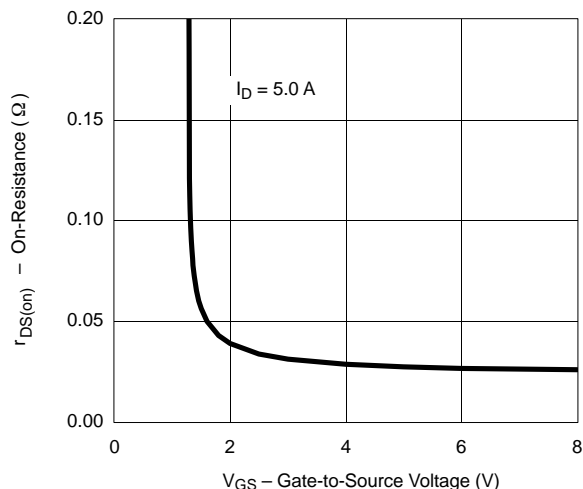


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

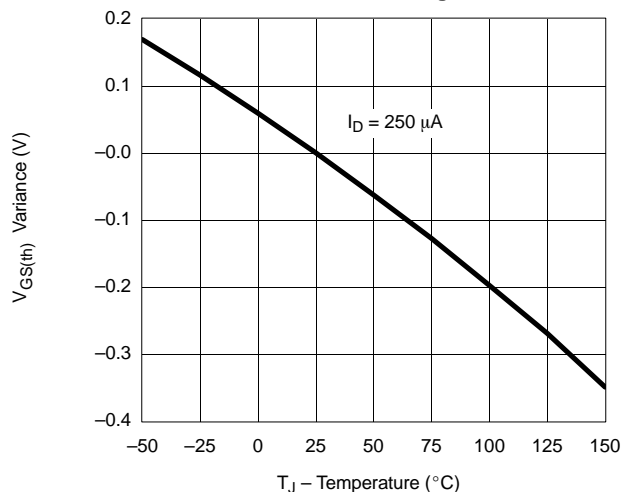
Source-Drain Diode Forward Voltage



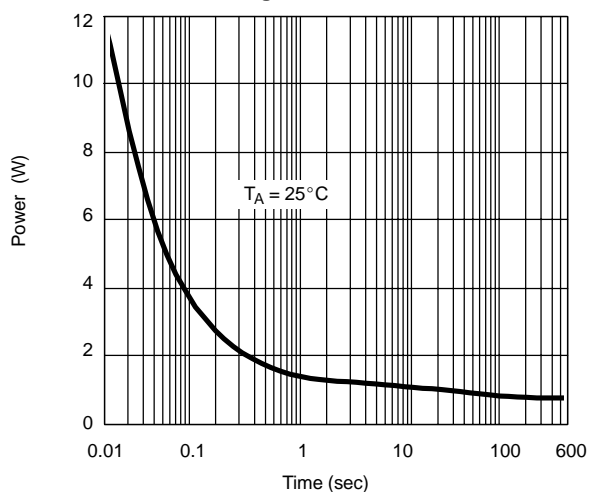
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient

